

产品规格书

批 准	审 核	校 核	编 制
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2018.03.02	2018.03.02	2018.03.02	2018.03.02

规格书更改履历:

序号	更改内容	履历号	更改时间	责任人
1	新规制定	000	2018. 03. 02	郑羿



KBT5401C

PNP Silicon Transistor

Descriptions

- General purpose amplifier
- High voltage application

Features

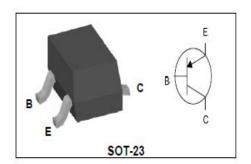
- High collector breakdown voltage: VCBO = -160V, VCEO = -160V
- Low collector saturation voltage: VCE(sat)=-0.5V(MAX.)
- Complementary pair with KBT5551C

Ordering Information

Type NO.	Marking	Package Code
KBT5401C	<u>NFN</u> □• ① ②	SOT-23

①Device Code ② Year& Week Code • Dalian

PIN Connection



Absolute maximum ratings

Ta=25°C

Characteristic	Symbol	Ratings	Unit
Collector-Base voltage	Vсво	-160	V
Collector-Emitter voltage	Vceo	-160	V
Emitter-Base voltage	Vево	-5	V
Collector current	I c	-600	mA
Collector dissipation	Pc	200	mW
Junction temperature	Tj	150	$^{\circ}$
Storage temperature	Tstg	-50~150	$^{\circ}$

KBT5401C

Electrical Characteristics

Ta=25 C

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base breakdown voltage	ВУсво	Ic=-100 μ A, Iε=0	-160	-	-	V
Collector-Emitter breakdown voltage	BVceo	Ic=-1mA, I _B =0	-160	-	-	V
Emitter-Base breakdown voltage	ВVево	I _E =-10 μ A, I _C =0	-5	-	-	V
Collector cut-off current	Ісво	Vcb=-120V, IE=0	-	-	-100	nA
Emitter cut-off current	Iево	V _{EB} =-3V, I _C =0	-	-	-100	nA
DC current gain	hfE (1)	Vce=-5V, Ic=-1mA	50	-		-
DC current gain	hfE (2)	Vce=-5V, Ic=-10mA	60	-	240	-
DC current gain	hfE (3)	Vce=-5V, Ic=-50mA	50	-		-
Collector-Emitter saturation voltage	VCE(sat)(1)	Ic=-10mA, I _B =-1mA	-	-	-0.2	V
Collector-Emitter saturation voltage	VCE(sat)(2)	Ic=-50mA, I _B =-5mA	-	-	-0.5	V
Base-Emitter saturation voltage	VBE(sat)(1)	Ic=-10mA, I _B =-1mA	-	-	-1	V
Base-Emitter saturation voltage	* VBE(sat)(2)	Ic=-50mA, I _B =-5mA	-	-	-1	V
Transition frequency	f⊤	Vce=-10V, Ic=-10mA	100	-	400	MHz
Collector output capacitance	Cob	VCB=-10V, IE=0, f=1MHz	-	-	6	pF

^{* :} Pulse Tester : Pulse Width $\, \leq \! 300 \, \mu \, \text{s}, \, \text{Duty Cycle} \, \leq \! 2.0 \%$

Electrical Characteristic Curves

Fig. 1 hFE - IC

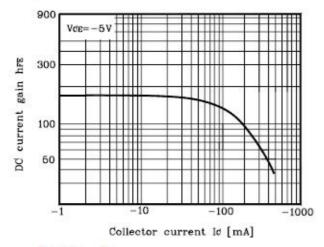


Fig. 3 fT - IC

Fig. 2 I_C - V_{BE}

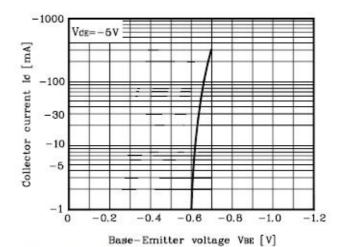
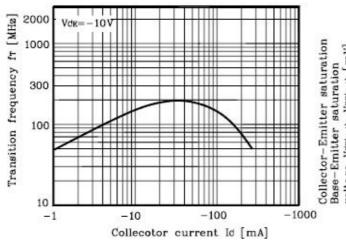
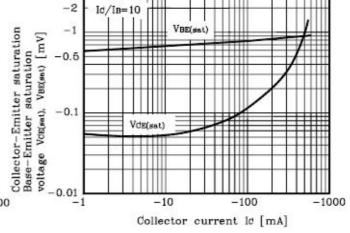
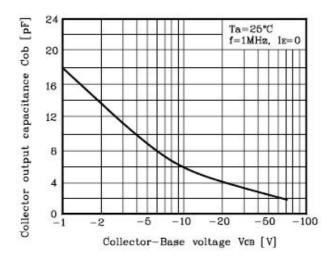


Fig. 4 VCE(sat), VBE(sat) - IC

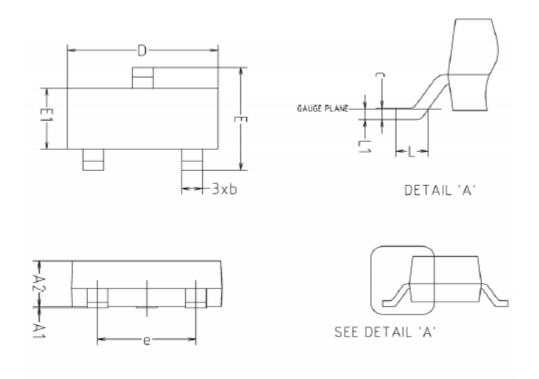






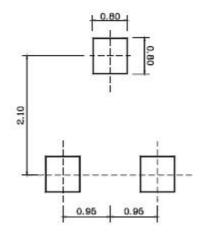


Outline Dimension



SYMBOL		NOTE		
JIIIDUL	MINIMUM	NOMINAL	MAXIMUM	NOTE
A1	0.00	-	0.10	
A2	0.82	-	1.02	
ь	0.39	0.42	0.45	
C	0.09	0.12	0.15	
D	2.80	2.90	3.00	
E	2.20	2.40	2.60	
E1	1.20	1.30	1.40	
e	1.90BSC			
L	0.20	-	-	
L1	0.12BSC			

*Recommend PCB solder land [Unit: mm]



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